L Number	Hits	Search Text	DB	Time stamp
-	558920	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:50
-	4784	capacitor and ((first adj conduct$4) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:51
-	98978	capacitor and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:51
-	2639	(capacitor and memory) and ((first adj conduct$4) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:51
-	167	((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:54
-	64	(((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:59
-	33	((((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)) and ((silicon adj nitride) with (first near2 oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:58
-	17	(((((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)) and ((silicon adj nitride) with (first near2 oxide))) and (second near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 12:00
-	16	((((((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)) and ((silicon adj nitride) with (first near2 oxide))) and (second near2 oxide)) and etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 12:04

L Number	Hits	Search Text	DB	Time stamp
-	558920	capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:50
-	4784	capacitor and ((first adj conduct$4) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:51
-	98978	capacitor and memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:51
-	2639	(capacitor and memory) and ((first adj conduct$4) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:51
-	167	((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:54
-	64	(((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:59
-	33	((((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)) and ((silicon adj nitride) with (first near2 oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 11:58
-	17	(((((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)) and ((silicon adj nitride) with (first near2 oxide))) and (second near2 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 12:00
-	16	((((((capacitor and memory) and ((first adj conduct$4) with substrate)) and ((silicon adj nitride) with (first adj conduct$4))) and (first near2 oxide)) and ((silicon adj nitride) with (first near2 oxide))) and (second near2 oxide)) and etch$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 12:04